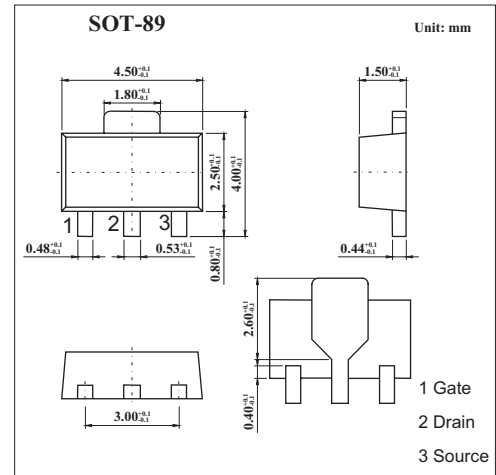


Silicon N-Channel MOSFET 2SK3065

■ Features

- Low on resistance.
 - High-speed switching.
 - Optimum for a pocket resource etc. because of undervoltage actuation (2.5V actuation).
 - Driving circuit is easy.
 - Easy to use parallel.
- It is strong to an electrostatic discharge.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Drain to source voltage	V _{DSS}	60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	2	A
	I _{dp} *	8	A
Power dissipation T _c =25°C	P _D	0.5	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* PW ≤ 10 μs, Duty Cycle ≤ 1%

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain to source breakdown voltage	V _{DSS}	I _D =1mA, V _{GS} =0	60			V
Drain cut-off current	I _{DSS}	V _{DS} =60V, V _{GS} =0			10	μA
Gate leakage current	I _{GSS}	V _{GS} =±20V, V _{DS} =0			±10	μA
Gate threshold voltage	V _{GS(th)}	V _{DS} =10V, I _D =1mA	0.8		1.5	V
Forward transfer admittance	Y _{fs}	V _{DS} =10V, I _D =1A	1.5			S
Drain to source on-state resistance	R _{DS(on)}	V _{GS} =4V, I _D =1A		0.25	0.32	Ω
		V _{GS} =2.5V, I _D =1A		0.35	0.45	Ω
Input capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0, f=1MHZ		160		pF
Output capacitance	C _{oss}			85		pF
Reverse transfer capacitance	C _{rss}			25		pF
Turn-on delay time	t _{on}	I _D =1A, V _{GS(on)} =4V, R _L =30Ω, V _{DD} =30V, R _G =10Ω		20		ns
Rise time	t _r			50		ns
Turn-off delay time	t _{off}			120		ns
Fall time	t _f			70		ns

■ Marking

Marking	KE
---------	----